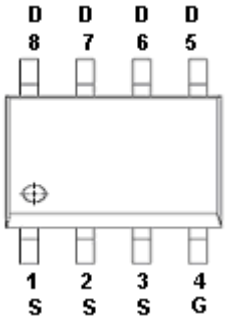
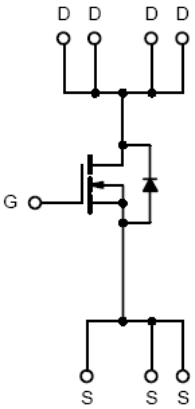
SPN4868
N-Channel Enhancement Mode MOSFET

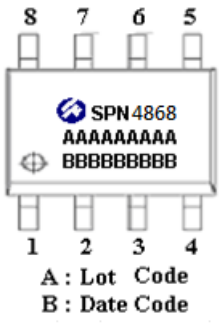
DESCRIPTION
The SPN4868 is the N-Channel logic enhancement mode power field effect transistors are produced using high cell density, DMOS trench technology.
This high density process is especially tailored to minimize on-state resistance.
These devices are particularly suited for low voltage application, notebook computer power management and other battery powered circuits where high efficiency and fast switching is required.

FEATURES
- 60V/6A,$R_{DS(ON)}$=21mΩ@V_{GS}=10V
- 60V/4A,$R_{DS(ON)}$=24mΩ@V_{GS}=4.5V
- Super high density cell design for extremely low $R_{DS\ (ON)}$
- Exceptional on-resistance and maximum DC current capability
- SOP-8 package design

APPLICATIONS
- Motor Drive
- Power Tools
- LED Lighting

PIN CONFIGURATION (SOP–8)




PART MARKING


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PIN DESCRIPTION

Pin	Symbol	Description
1	S	Source
2	S	Source
3	S	Source
4	G	Gate
5	D	Drain
6	D	Drain
7	D	Drain
8	D	Drain

ORDERING INFORMATION

Part Number	Package	Part Marking
SPN4868S8RGB	SOP-8	SPN4868

※ SPN4868S8RGB : 13" Tape Reel ; Pb – Free; Halogen - Free

ABSOULTE MAXIMUM RATINGS

(T_A=25℃ Unless otherwise noted)

Parameter		Symbol	Typical	Unit
Drain-Source Voltage		V_{DSS}	60	V
Gate –Source Voltage		V_{GSS}	±20	V
Continuous Drain Current(T_J=150℃)	T_C=25℃	I_D	6	A
	T_C=100℃		3.6	
Pulsed Drain Current		I_{DM}	24	A
Continuous Source Current(Diode Conduction)		I_S	6	A
Power Dissipation	T_A=25℃	P_D	1.47	W
Operating Junction Temperature		T_J	-55/150	℃
Storage Temperature Range		T_{STG}	-55/150	℃
Thermal Resistance-Junction to Ambient		$R_{\theta JA}$	62	℃/W
Thermal Resistance-Junction to Case		$R_{\theta JC}$	2.8	℃/W

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ELECTRICAL CHARACTERISTICS

(T_A=25℃ Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250uA	60			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_{DS}=25uA	1.2	1.8	2.5	
Gate Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS}=±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=60V,V_{GS}=0V, T_J=25℃			1	uA
		V_{DS}=48V,V_{GS}=0V, T_J=125℃			10	
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=6A		17	21	mΩ
		V_{GS}=4.5V, I_D=4A		20	24	
Forward Transconductance	gfs	V_{DS}=10V, I_D=10A		9		S
Diode Forward Voltage	V_{SD}	I_F=1A,V_{GS}=0V			1	V
Dynamic						
Total Gate Charge	Q_g	V_{DS}=30V,V_{GS}=10V, I_D=15A		28	42	nC
Gate-Source Charge	Q_{gs}			3.5	7	
Gate-Drain Charge	Q_{gd}			6.5	10	
Input Capacitance	C_{iss}	V_{GS}=0V,V_{DS}=20V, F=1MHz		1680	2440	pF
Output Capacitance	C_{oss}			115	170	
Reverse Transfer Capacitance	C_{rss}			85	125	
Turn-On Time	$t_{d(on)}$	(V_{DD}=30V,I_D=-1A, V_{GEN}=10V,R_G=6Ω)		7.2	14	nS
	t_r			38	72	
Turn-Off Time	$t_{d(off)}$			34	65	
	t_f			8.2	16	

TYPICAL CHARACTERISTICS

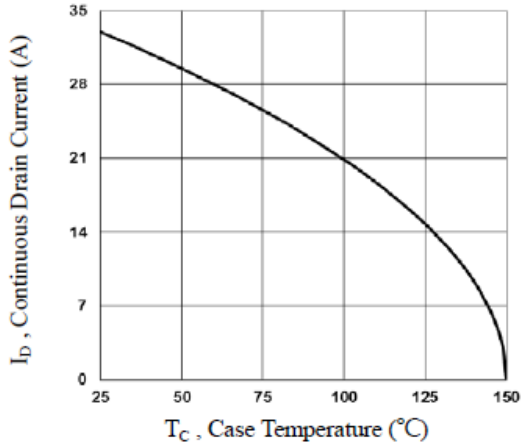

Fig.1 Continuous Drain Current vs. T_c

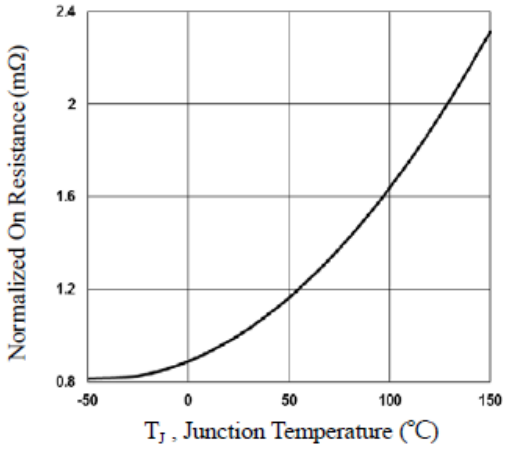

Fig.2 Normalized RDSON vs. T_J

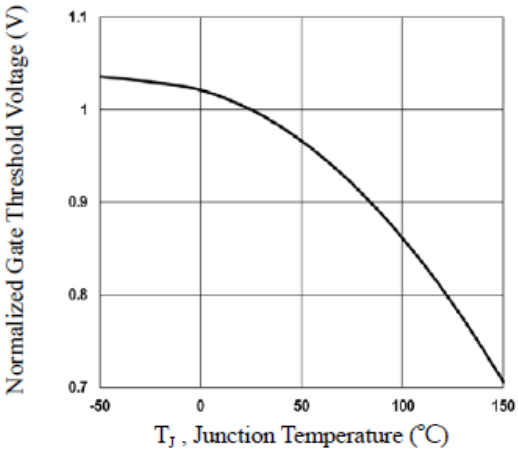

Fig.3 Normalized V_{th} vs. T_J

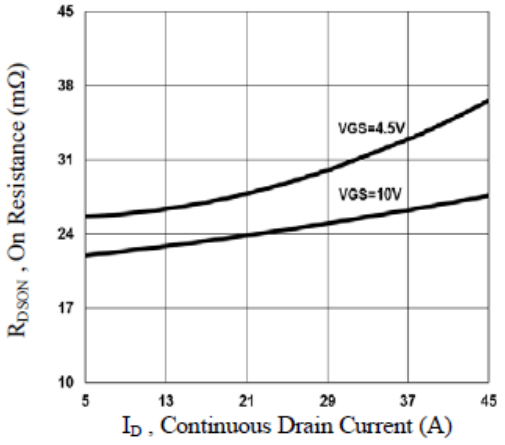

Fig.4 RDSON vs. Continuous Drain Current

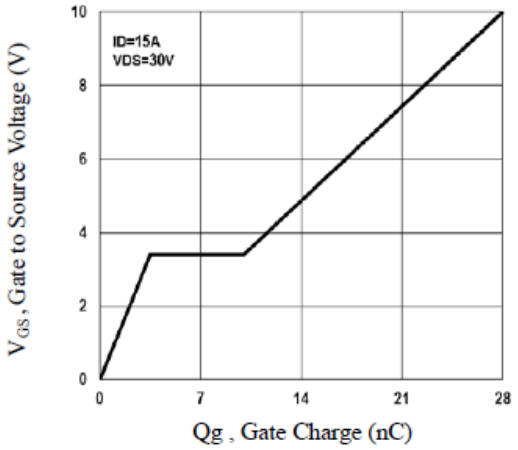

Fig.5 Gate Charge Waveform

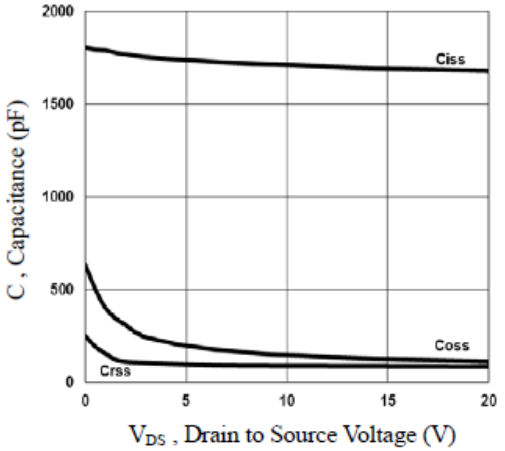

Fig.6 Capacitance Characteristics

TYPICAL CHARACTERISTICS

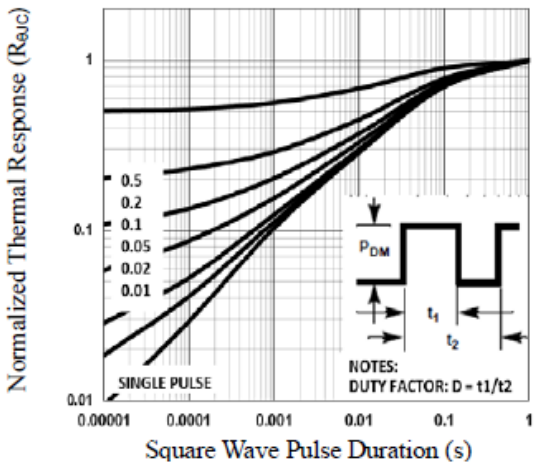

Fig.7 Normalized Transient Impedance

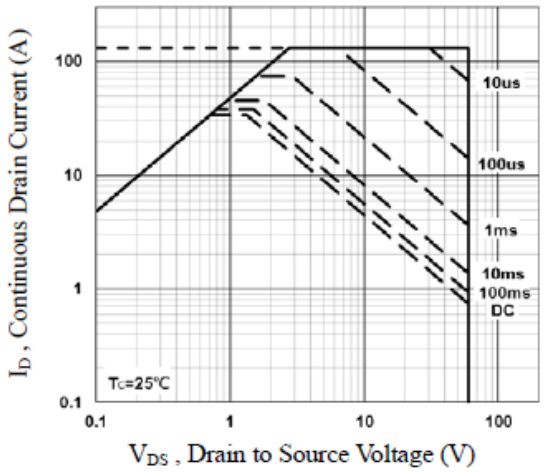

Fig.8 Maximum Safe Operation Area

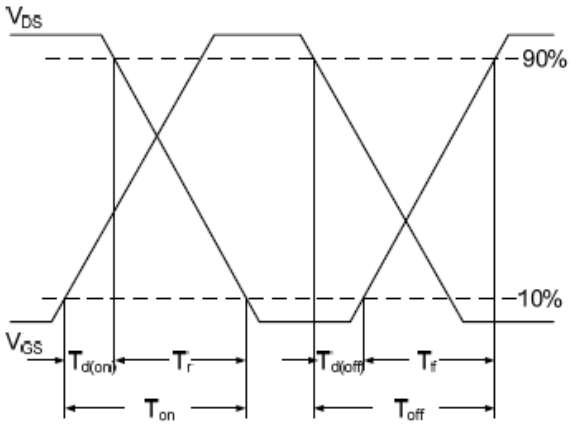

Fig.9 Switching Time Waveform

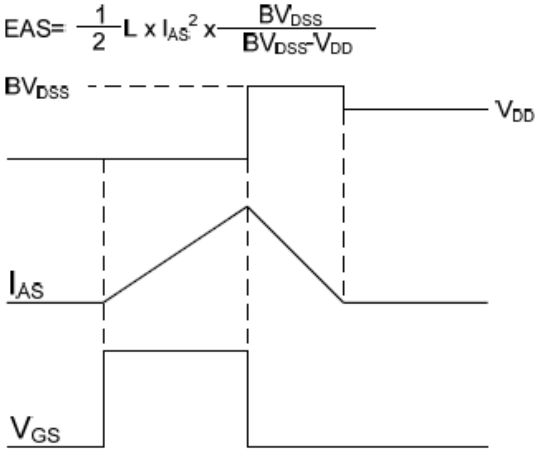

Fig.10 EAS Waveform

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